Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS

Claims 1-13. (Cancelled)

Claim 14. (Currently Amended) A power semiconductor device with trench gates comprising:

a) a semiconductor substrate;

b) a source layer on one surface of [[the]] said substrate and comprising a high concentration of a dopant of [[one]] a first polarity;

~~a region lightly doped with said one polarity;~~

c) a single drain region on the other surface of [[the]] said substrate;

d) a well layer beneath [[the]] said source layer doped with a dopant of a second polarity opposite to said first polarity;

e) a region lightly doped with said one polarity positioned above said drain region and below said well layer;

f) a plurality of trenches penetrating [[the]] said source layer and terminating in said region lightly doped with said one polarity, said trenches substantially filled with conductive material;

g) a highly conductive layer on the surface of [[the]] said source layer comprising a material reacted from a metal and ~~the semiconductor~~ said substrate which forms a highly conductive path extending from a first of said plurality of trenches to a second of said plurality of trenches;

h) an insulating layer on [[the]] said highly conductive layer and on [[the]] said conductive material in [[the]] said trenches;

i) vias formed in [[the]] said insulating layer and extending to [[the]] said highly conductive layer ~~on the source layer~~; and

j) _____conductive material filling [[the]] said vias for contacting [[the]] said highly conductive layer.

Claims 15-19. (Cancelled).

Claim 20. (Currently Amended) The power semiconductor device of claim 14 wherein [[the]] said trenches are filled with polysilicon and the top surface of [[the]] said polysilicon is covered with a highly conductive material reacted from a metal and ~~the semiconductor substrate~~ said polysilicon.

Claim 21. (Currently Amended) The power semiconductor device of claim 14 wherein [[the]] said highly conductive layer is a silicide.

Claim 22. (Cancelled).

Claim 23. (Currently Amended) The power semiconductor device of ~~claim 20 or 21~~ claim 21 wherein [[the]] said silicide is reacted from platinum or titanium.

Claim 24. (Currently Amended) The power semiconductor device of claim 14 wherein [[the]] said insulating material on [[the]] said highly conductive layer is BPSG, PSG, silicon dioxide or silicon nitride.

Claim 25. (Currently Amended) The power semiconductor device of claim 14 wherein [[the]] said trenches are lined with a trench wall insulating material and [[the]] said insulating material on [[the]] said highly conductive layer contacts the ends of [[the]] said trench wall insulating [[layer]] layers lining [[the]] said walls of [[the]] said trenches.

Claim 26. (Currently Amended) The power semiconductor device of claim 14 wherein one or more vias terminated on [[the]] said surface of [[the]] said highly conductive layer ~~for making~~ make electrical contact between [[the]] said highly conductive source layer ~~and the~~ and conductive material filling ~~the via(s)~~ said vias.